

1SS345

Silicon Epitaxial Schottky Barrier Diode

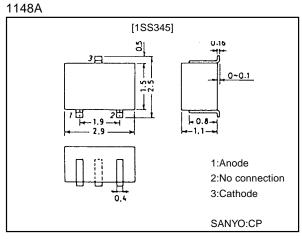
UHF Detector, Mixer Applications

Features

- · Small interterminal capacitance (C=0.45pF typ).
- \cdot Low forward voltage and excellent detection efficiency (V_F=0.35V max)
- · High breakdown voltage (V_R =55V).
- Very small-sized package permitting the 1SS345applied sets to be made small and slim.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

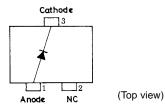
Parameter	Symbol	Conditions	Ratings	Unit
Reverse Voltage	VR		55	V
Forward Current	۱ _F		10	mA
Power Dissipation	Р		150	mW
Junction Temperature	Tj		125	°C
Storage Temperature	Tstg		-55 to +125	°C
Reverse Burning	Во	(C=25pF)	2	erg

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Voltage	VR	I _F =1mA			0.35	V
Forward Current	١ _F	V _F =1V	10			mA
Reverse Voltage	VR	I _R =100μA	55			V
Reverse Current	I _R	V _R =40V			50	μA
Interterminal Capacitance	С	V _R =10V, f=1MHz		0.45		pF

· Marking:AH

Electrical Connection



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